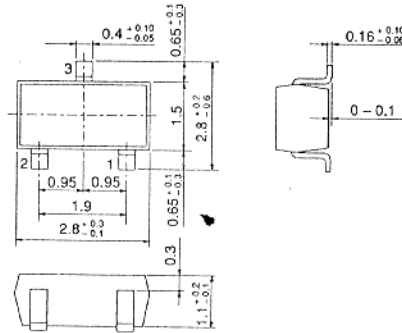


2SA1468

SILICON PNP EPITAXIAL
HIGH VOLTAGE AMPLIFIER



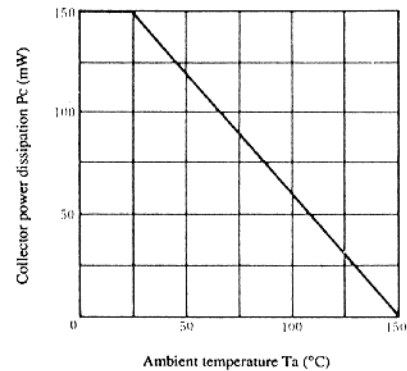
1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1468	Unit
Collector to base voltage	V _{CB0}	-180	V
Collector to emitter voltage	V _{CE0}	-180	V
Emitter to base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

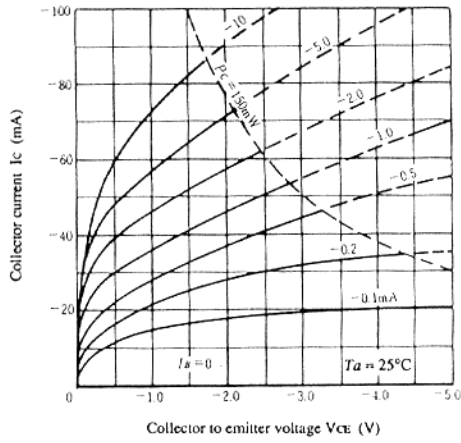
Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CB0}	I _C = -10μA, I _E = 0	-180	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CE0}	I _C = -0.5mA, R _{BE} = ∞	-180	—	—	V
Emitter to base breakdown voltage	V _{(BR)EB0}	I _E = -10μA, I _C = 0	-5	—	—	V
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	100	—	320	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -30mA, I _B = -3mA**	—	—	-0.5	V
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	—	-1.0	V
Gain bandwidth product	f _r	V _{CE} = -12V, I _C = -10mA	—	200	—	MHz
Collector output capacitance	C _{ob}	V _{CE} = -10V, I _E = 0, f = 1MHz	—	3.5	—	pF

* The 2SA1468 is grouped by h_{FE} as follows.

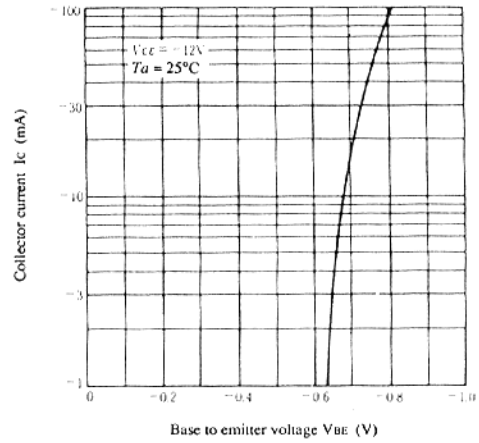
Grade	B	C
Mark	INB	INC
h _{FE}	100 to 200	160 to 320

2SA1468

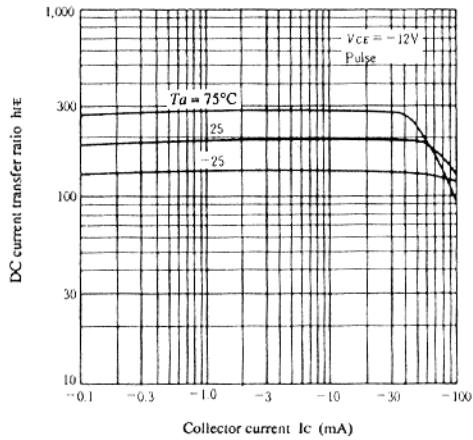
TYPICAL OUTPUT CHARACTERISTICS



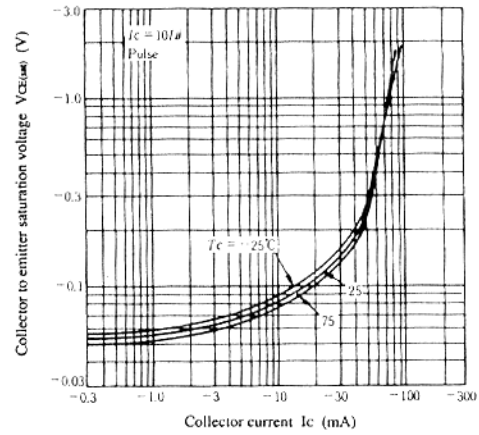
TYPICAL TRANSFER CHARACTERISTICS



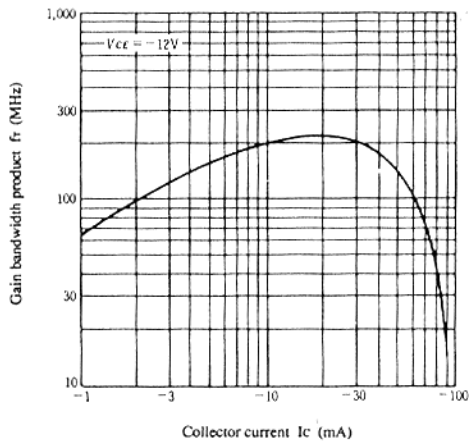
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE

